



MA6BA6 Süss Mask Aligner

Responsible

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System Description

Mask aligner for photolithography with back side alignment.

Sample size:

Chucks for small chips up to 6inch wafers

Substrates and Materials allowed and not allowed:

Generally silicon and glass wafer are used. Please ask the tool responsible person in case of special wafer material.

Available exposure modes:

Vacuum contact, Hard contact, Soft contact, Proximity exposure

UV wavelength:

350W Hg lamp with broadband i-line 365 nm and h-line 405 nm.

CIC controller:

CP – broadband constant power (variable intensity, must be measured before exposure)

Ch1 – broadband, with fixed intensity for i-line (for negative resist exposure)

CH2 – broadband, with fixed intensity for h-line (for positive resist exposure)